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Application Serial No: 10/509,463

Responsive to the final Office Action mailed on: April 20, 2009

IN THE CLAIMS**Amendments To The Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-4. (Cancelled)

5. (Currently Amended) An apparatus for manufacturing a thin film in which the thin film is formed on a supporting base, comprising:

a vacuum container that houses the supporting base;

an electron beam evaporation source that is arranged in the vacuum container so as to face a surface to be vapor-deposited of the supporting base and contains a first thin film material;

an electron beam source that is arranged in the vacuum container and emits an accelerated electron beam to be used to evaporate the first thin film material by heating using an electron beam heating method; and

a resistance heating evaporation source that is arranged in the vacuum container so as to face the surface to be vapor-deposited and evaporates a second thin film material by heating using a resistance heating method,

wherein the electron beam evaporation source, the electron beam source and the resistance heating evaporation source are arranged so that a path along which the accelerated electron beam emitted from the electron beam source reaches the electron beam evaporation source intersects with a line segment connecting the resistance heating evaporation source with the surface to be vapor-deposited,

wherein each of the first thin film material and the second thin film material is a metal film material, and

wherein the electron beam source and the electron beam evaporation source are arranged so as to be opposed to each other with respect to a straight line connecting the resistance heating evaporation source with the surface to be vapor-deposited.

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6. (Cancelled)

7. (Original) The apparatus according to claim 5, further comprising a nozzle for introducing a reactive gas in a portion on the surface to be vapor-deposited in which the thin film is to be formed.

8. (Original) The apparatus according to claim 5, further comprising a bias device for applying a bias voltage to the surface to be vapor-deposited.

9. (Original) The apparatus according to claim 5, wherein the electron beam evaporation source, the electron beam source and the resistance heating evaporation source are arranged substantially on the same plane.

10. (Withdrawn) A method for manufacturing a thin film in which the thin film is manufactured using an apparatus as claimed in claim 5.

11. (Withdrawn) The method according to claim 10, wherein the first thin film material is Co and the second thin film is Li.